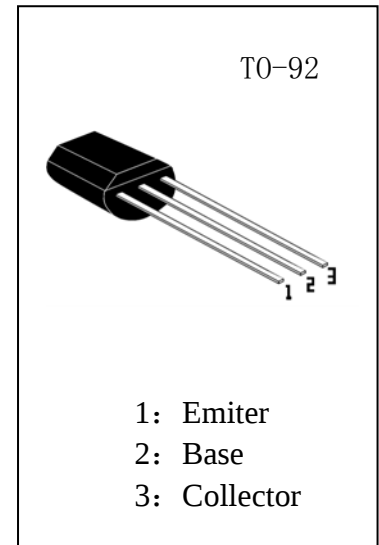


低压晶体管

- 高集电极电流 $I_c=1500\text{mA}$
- 高耗散功率 $P_c=1000\text{mW}$
- 与 8550A 对管

极限参数(Absolute Maximum Ratings) $T_a=25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	40	V
Collector-Emitter Voltage	V_{ceo}	25	V
Emitter-Base Voltage	V_{ebo}	6	V
Collector Current	I_c	1500	mA
Collector Dissipation	P_c	1000	m W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$



电性能(Electrical Characteristic) $T_a=25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=100\mu\text{A}$ $I_e=0$	40			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=2\text{mA}$ $I_b=0$	25			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=100\mu\text{A}$ $I_c=0$	6			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=35\text{V}$, $I_e=0$			100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=6\text{V}$, $I_c=0$			100	nA
I_{ceo}	Collector Cutoff Current	$V_{ce}=20\text{V}$, $I_b=0$			10	μA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c=800\text{mA}$, $I_b=80\text{mA}$		0.26	0.5	V
$V_{ce(sat)2}$	Base-Emitter Saturation Voltage	$I_c=1500\text{mA}$, $I_b=150\text{mA}$			0.5	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c=800\text{mA}$, $I_b=80\text{mA}$		0.98	1.2	V
$V_{be(on)}$	Base-Emitter On Voltage	$V_{ce}=1\text{V}$, $I_c=10\text{mA}$		0.66	1	V
H_{fe1}	DC Current Gain	$V_{ce}=1\text{V}$, $I_c=5\text{mA}$	45			
H_{fe2}	DC Current Gain	$V_{ce}=1\text{V}$, $I_c=100\text{mA}$	80		300	
H_{fe3}	DC Current Gain	$V_{ce}=1\text{V}$, $I_c=800\text{mA}$	80			
C_{ob}	Output Capacitance	$V_{cb}=10\text{V}$, $I_e=0$, $f=1\text{MHz}$		9	15	PF
f_T	Current Gain-Bandwidth product	$V_{ce}=10\text{V}$, $I_c=50\text{mA}$,	100	200		MHz

CLASS	B	C	D		
Hfe2	80-120	120-160-200	160-200	200-250	250-300